

**Notice of References Cited**Application/Control No.  
**09/603,941**Applicant(s)/Patent Under Review  
**Bao et al.**Examiner  
**George C. Eckert II**Art Unit  
**2815**

Page 1 of 1

**U.S. PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Name	Classification <sup>2</sup>	
A	4,278,804	7/1981	Ashby et al.	556	436
B	4,756,977	7/1988	Haluska et al.	428	704
C	5,321,102	6/1994	Loy et al.	525	474
D	5,500,537	3/1996	Tsumura et al.	257	40
E	5,976,966	11/1999	Inoue	438	618
F	6,054,769	4/2000	Jeng	257	758
G	6,136,729	10/2000	Hopper et al.	438	778
H	6,153,833	11/2000	Dawson et al.	174	255
I	6,214,748	4/2001	Kobayashi et al.	438	782
J					
K					
L					
M					

**FOREIGN PATENT DOCUMENTS**

	Document Number Country Code-Number-Kind Code	Date MM-YYYY <sup>1</sup>	Country	Name	Classification <sup>2</sup>	
N	4-4-228415	8/1992	Japan	Baney et al.	C01B	33/12
O						
P						
Q						
R						
S						
T						

**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Allman et al., The Material Characteristics of a New Methyl-Phenyl Silsesquioxane Spin-On Glass for Use in a Global Non-Etchback Interconnect Planarization Process, June 1991, IEEE, VMIC Conference, pp. 373-75.
V	Jeng et al., Highly Porous Interlayer Dielectric For Interconnect Capacitance Reduction, 1995, Symposium on VLSI Technology Digest of Technical Papers, pp. 61-62.
W	
X	

<sup>1</sup> A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).<sup>1</sup> Dates in MM-YYYY format are publication dates.<sup>2</sup> Classifications may be U.S. or foreign.